



°C



	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					



FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)
 $P_T(AV)/P_F(AV)(W)$

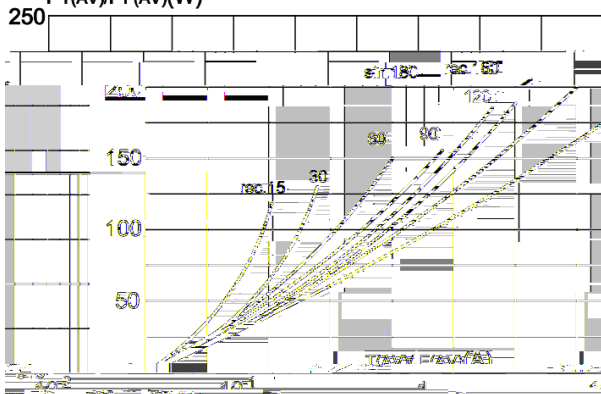


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)
 $R_{th(j-c)}(^{\circ}C/W)$

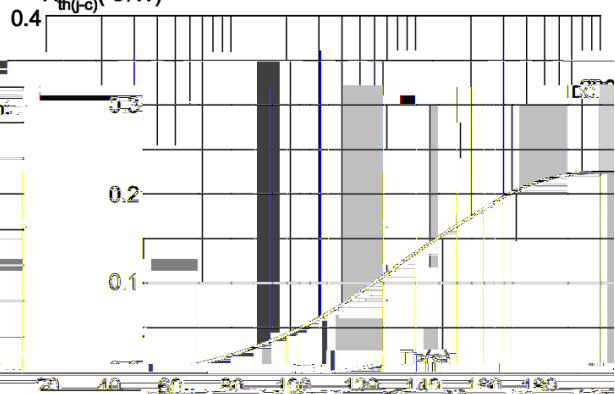


FIG.3: Forward characteristics
(per thyristor or diode)

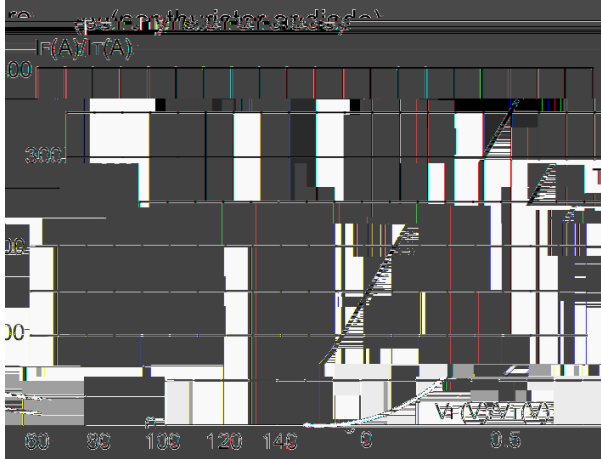


FIG.4: Relative variations of gate trigger current, holding current and latching current vs. junction temperature
($I_{GT}(T)/I_{GT}(T=25^{\circ}C)$)

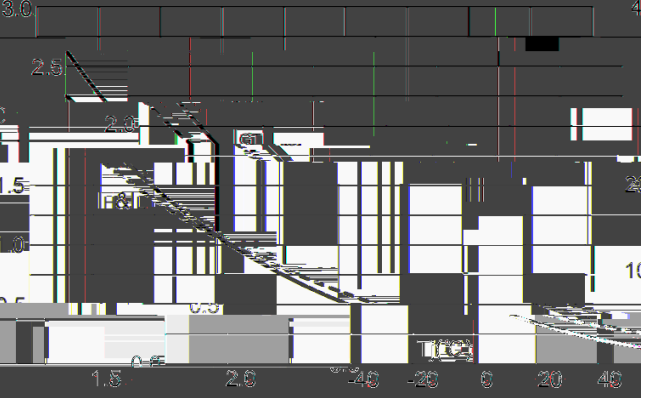


FIG.5: Gate trigger characteristics

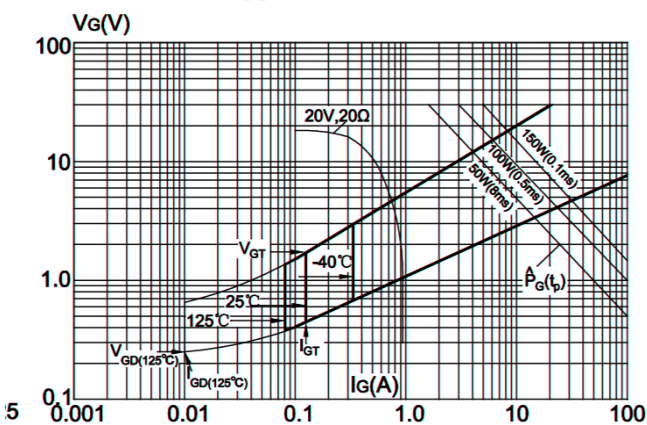


FIG.6: Forward current vs. case temperature
 $I_F(AV)(A)$ (per thyristor or diode)

